

# MBD101G, MMBD101LT1G

## Schottky Barrier Diodes

Designed primarily for UHF mixer applications but suitable also for use in detector and ultra-fast switching circuits. Supplied in an inexpensive plastic package for low-cost, high-volume consumer requirements. Also available in Surface Mount package.

### Features

- Low Noise Figure – 6.0 dB Typ @ 1.0 GHz
- Very Low Capacitance – Less Than 1.0 pF
- High Forward Conductance – 0.5 V (Typ) @  $I_F = 10$  mA
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	7.0	V
Forward Power Dissipation $T_A = 25^\circ\text{C}$	$P_F$	280 225	mW
Derate above $25^\circ\text{C}$		2.2 1.8	mW/ $^\circ\text{C}$
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu\text{A}$ )	$V_{(BR)R}$	7.0	10	-	V
Diode Capacitance ( $V_R = 0$ , $f = 1.0$ MHz, Note 1, page 2)	$C_D$	-	0.88	1.0	pF
Forward Voltage ( $I_F = 10$ mA)	$V_F$	-	0.5	0.6	V
Reverse Leakage ( $V_R = 3.0$ V)	$I_R$	-	0.02	0.25	$\mu\text{A}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

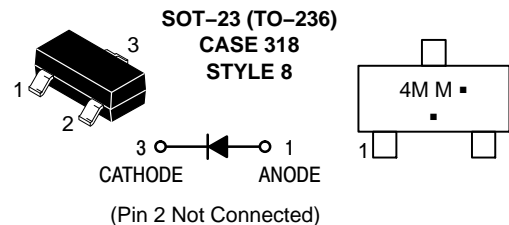
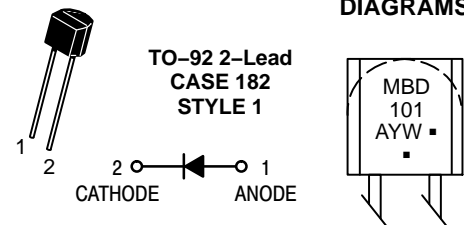


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## SILICON SCHOTTKY BARRIER DIODES

### MARKING DIAGRAMS



A = Assembly Location  
Y = Year  
W = Work Week  
4M = Device Code (SOT-23)  
M = Date Code\*  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)  
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MBD101G	TO-92 (Pb-Free)	5000 Units / Box
MMBD101LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MBD101G, MMBD101LT1G

## TYPICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless noted)

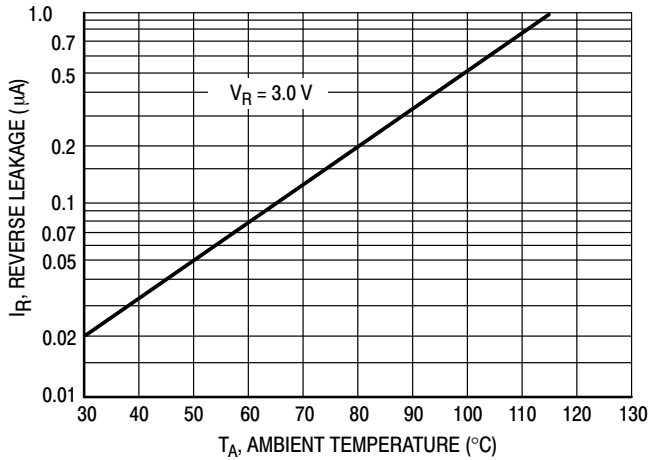


Figure 1. Reverse Leakage

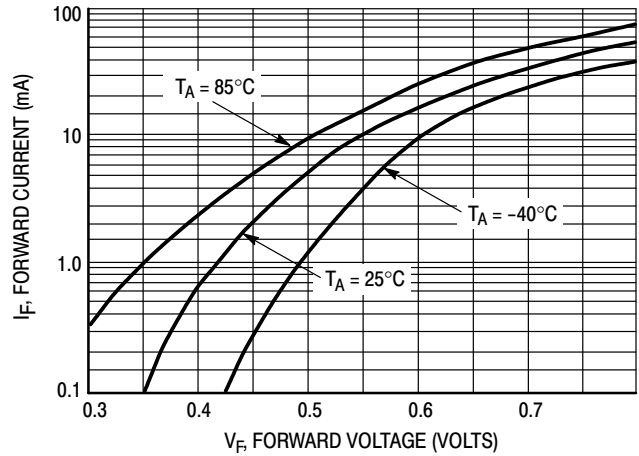


Figure 2. Forward Voltage

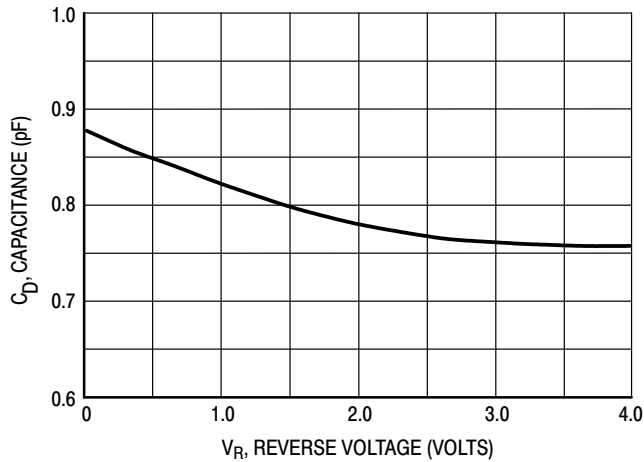


Figure 3. Capacitance

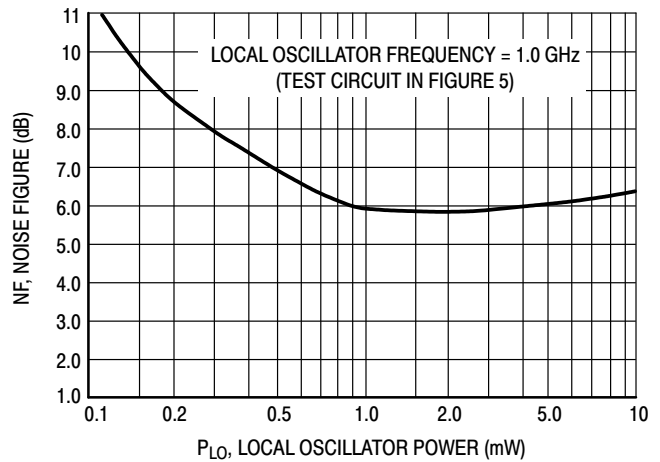


Figure 4. Noise Figure

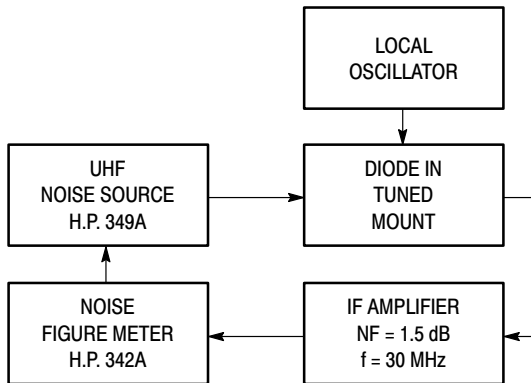


Figure 5. Noise Figure Test Circuit

### NOTES ON TESTING AND SPECIFICATIONS

- Note 1 —  $C_D$  is measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).
- Note 2 — Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB,  $f = 30$  MHz, see Figure 5.
- Note 3 —  $L_S$  is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

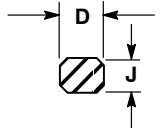
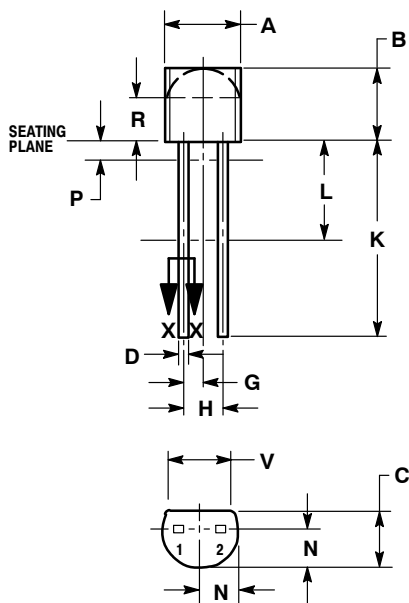
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TO-92 (TO-226)  
CASE 182-06  
ISSUE L

DATE 04/18/1998

SCALE 1:1



SECTION X-X

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

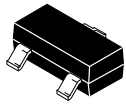
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.050 BSC		1.27 BSC	
H	0.100 BSC		2.54 BSC	
J	0.014	0.016	0.36	0.41
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.03	2.66
P	---	0.050	---	1.27
R	0.115	---	2.93	---
V	0.135	---	3.43	---

- STYLE 1: PIN 1. ANODE  
2. CATHODE
- STYLE 2: PIN 1. CATHODE  
2. ANODE
- STYLE 3: PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2
- STYLE 4: CANCELLED
- STYLE 5: PIN 1. INPUT  
2. OUTPUT

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DESCRIPTION:	TO-92 (TO-226)	PAGE 1 OF 1

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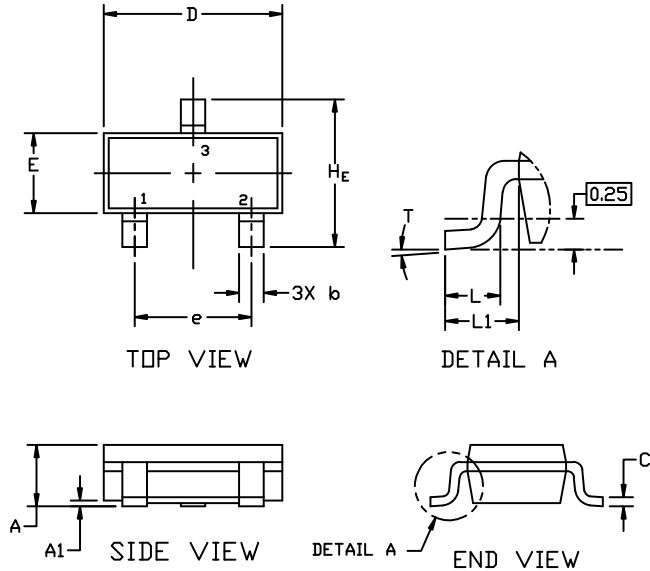
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)**  
CASE 318  
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

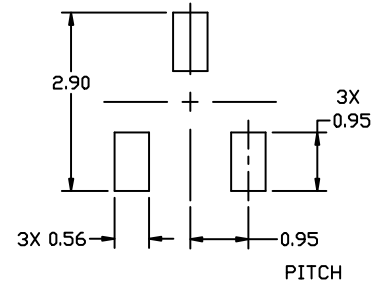
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED MOUNTING FOOTPRINT**

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



### SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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